P-Channel 120-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

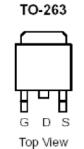
Typical Applications:

- · White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY | | | | |
|---------------------|-----------------------------|--------------------|--|--|
| V _{DS} (V) | $r_{DS(on)}(m\Omega)$ | I _D (A) | | |
| -120 | 42 @ V _{GS} = -10V | -69 | | |
| -120 | $48 @ V_{GS} = -5.5V$ | -65 | | |







| ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED) | | | | | | | |
|---|----------------------|-------------------|-------------|-------|--|--|--|
| Parameter | | | Limit | Units | | | |
| Drain-Source Voltage | | | -120 | V | | | |
| Gate-Source Voltage | V_{GS} | ±20 | \ \ \ \ \ \ | | | | |
| Continuous Drain Current a | T _C =25°C | I _D | -69 | А | | | |
| Pulsed Drain Current ^b | | I _{DM} | -280 | Α | | | |
| Continuous Source Current (Diode Conduction) a | T _C =25°C | I _S | -69 | Α | | | |
| Power Dissipation ^a | T _C =25°C | P_D | 300 | W | | | |
| Operating Junction and Storage Temperature Range | | T_J , T_{stg} | -55 to 175 | °C | | | |

| THERMAL RESISTANCE RATINGS | | | | | | | |
|-------------------------------|-----------------|---------|-------|--|--|--|--|
| Parameter | Symbol | Maximum | Units | | | | |
| Maximum Junction-to-Ambient ° | $R_{\theta JA}$ | 62.5 | °C/W | | | | |
| Maximum Junction-to-Case | $R_{\theta JC}$ | 0.5 | C/VV | | | | |

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

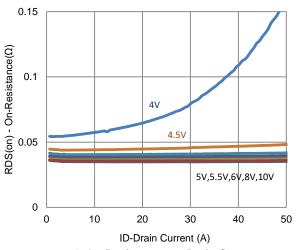
| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit | |
|---|---------------------|---|---|-------|-------|------|--|
| Static | | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$ | -1 | | | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ±100 | nA | |
| Zero Gate Voltage Drain Current | l | $V_{DS} = -96 \text{ V}, V_{GS} = 0 \text{ V}$ | | | -1 uA | | |
| Zelo Gale Voltage Dialii Cullent | I _{DSS} | $V_{DS} = -96 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | $_{OS} = -96 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55^{\circ}\text{C}$ | | -10 | uA | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$ | -90 | | | Α | |
| Drain-Source On-Resistance ^a | r | $V_{GS} = -10 \text{ V}, I_D = -30 \text{ A}$ | | | 42 | mO. | |
| Drain-Source On-Resistance | r _{DS(on)} | $V_{GS} = -4.5 \text{ V}, I_{D} = -25 \text{ A}$ | | | 48 | mΩ | |
| Forward Transconductance a | g_{fs} | $V_{DS} = -50 \text{ V}, I_{D} = -30 \text{ A}$ | | 49 | | S | |
| Diode Forward Voltage ^a | V_{SD} | $I_S = -30 \text{ A}, V_{GS} = 0 \text{ V}$ | | -0.88 | | V | |
| | | Dynamic ^b | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -60 \text{ V}, V_{GS} = -4.5 \text{ V},$ | | 78 | | nC | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = -600 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -30 \text{ A}$ | | 24 | | | |
| Gate-Drain Charge | Q_gd | 10 = 30 // | | 32 | | | |
| Turn-On Delay Time | t _{d(on)} | V 60 V D = 2.0 | | 19 | | | |
| Rise Time | t _r | $V_{DS} = -60 \text{ V}, R_{L} = 2 \Omega,$ $I_{D} = -30 \text{ A},$ | | 21 | | no | |
| Turn-Off Delay Time | t _{d(off)} | $V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$ | | 117 | | ns | |
| Fall Time | t _f | VGEN - 10 V, NGEN 0 12 | | 62 | | | |
| Input Capacitance | C_{iss} | | | 3622 | | pF | |
| Output Capacitance | C _{oss} | $V_{DS} = -50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$ | | 199 | | | |
| Reverse Transfer Capacitance | C_{rss} | | | 134 | | | |

Notes

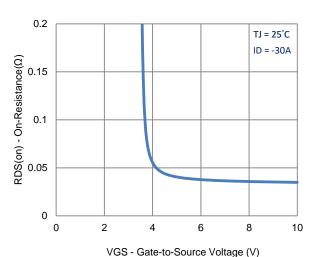
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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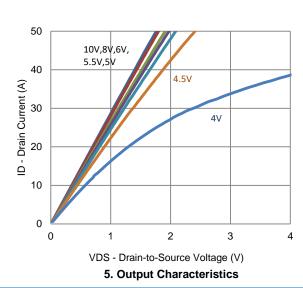
Typical Electrical Characteristics

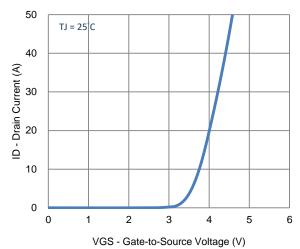


1. On-Resistance vs. Drain Current

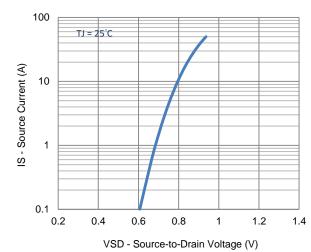


3. On-Resistance vs. Gate-to-Source Voltage

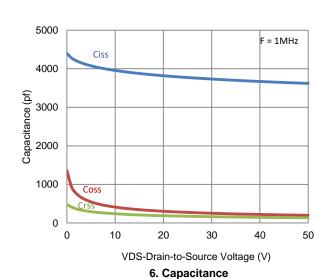




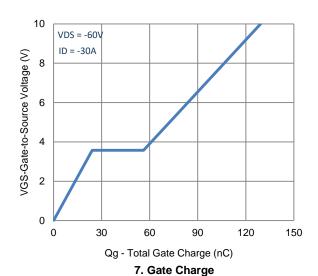
2. Transfer Characteristics

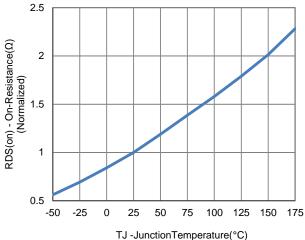


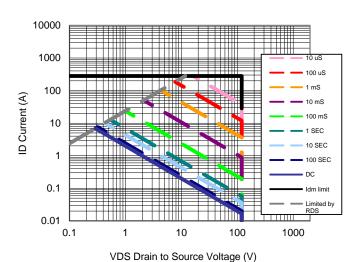
4. Drain-to-Source Forward Voltage



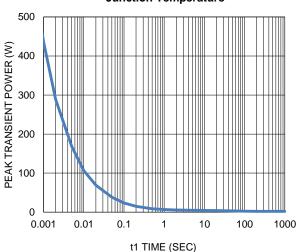
Typical Electrical Characteristics





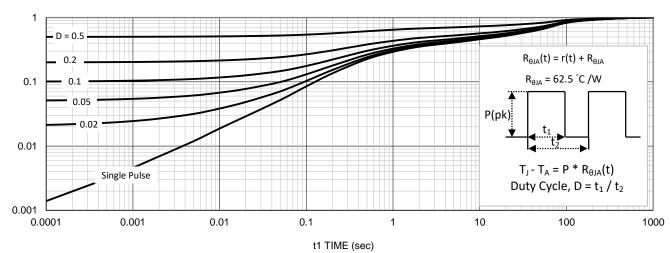


8. Normalized On-Resistance Vs
Junction Temperature



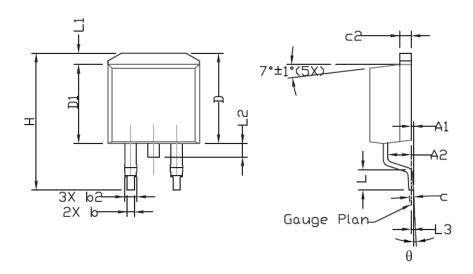
9. Safe Operating Area

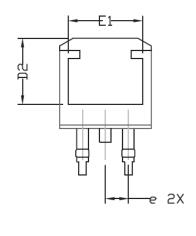
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





| CVAREI | DIMENSIONAL REQMTS | | | INCH | ES REQMTS | | |
|--------|--------------------|-------|-------|-------|-----------|-------|--|
| SYMBOL | MIN | NDM | MAX | MIN | NDM | MAX | |
| Α | 4,30 | 4.57 | 4,72 | 0.169 | 0.180 | 0.186 | |
| A1 | 0 | - | 0,25 | 0 | - | 0.010 | |
| A2 | 2,47 | 2.57 | 2,67 | 0.097 | 0.101 | 0.105 | |
| b | 0.69 | 0,813 | 0.94 | 0.027 | 0.032 | 0.037 | |
| b2 | 1.17 | 1,27 | 1,45 | 0.046 | 0.050 | 0.057 | |
| C | 0.48 | 0,50 | 0.60 | 0.019 | 0.020 | 0.024 | |
| c2 | 1,17 | 1.27 | 1.37 | 0.046 | 0.050 | 0,054 | |
| D | 9.80 | 10.05 | 10,30 | 0.386 | 0,396 | 0.406 | |
| D1 | 8,64 | 8.78 | 9,65 | 0.340 | 0,346 | 0,380 | |
| D2 | 7.12 | 7.37 | 7,62 | 0.280 | 0,290 | 0,300 | |
| E | 9,70 | 10.15 | 10.54 | 0.382 | 0,400 | 0.415 | |
| E1 | 8,00 | 8.20 | 8,40 | 0.315 | 0,323 | 0.331 | |
| е | 2,54 BSC | | | 0. | 0.100 BSC | | |
| H | 14.99 | 15,24 | 15,49 | 0.590 | 0.600 | 0.610 | |
| L | 1,78 | 2.29 | 2.79 | 0.070 | 0.090 | 0.110 | |
| L1 | 1,02 | 1.27 | 1.52 | 0.040 | 0,050 | 0,060 | |
| L2 | | | 1.75 | | | 0.069 | |
| L3 | | 0,254 | | | 0.010 | | |
| θ | 0. | | 8• | 0° | | 8° | |